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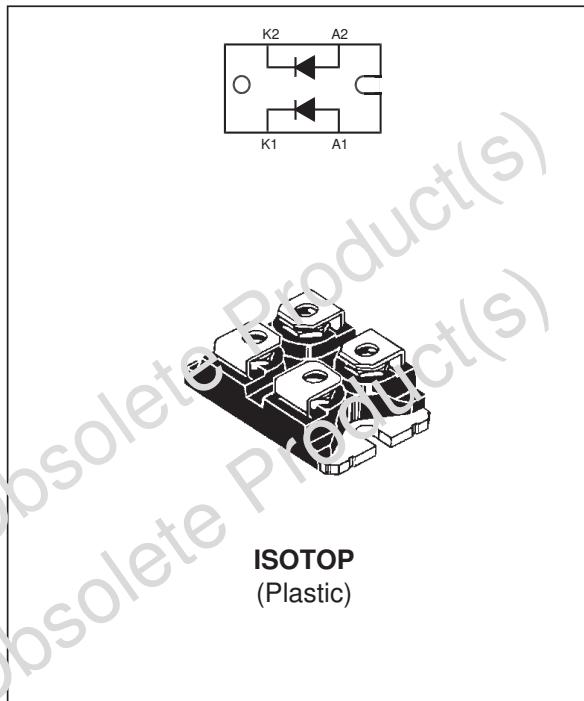
HIGH EFFICIENCY FAST RECOVERY RECTIFIER DIODES

FEATURES

- SUITED FOR SMPS
- VERY LOW FORWARD LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- HIGH SURGE CURRENT CAPABILITY
- HIGH AVALANCHE ENERGY CAPABILITY
- INSULATED :
Insulating voltage = 2500 V_{RMS}
Capacitance = 55 pF

DESCRIPTION

Dual rectifier suited for switchmode power supply and high frequency DC to DC converters.
Packaged in ISOTOP™ this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter			Value	Unit
I _{F(RMS)}	RMS forward current		Per diode	150	A
I _{F(AV)}	Average forward current $\delta = 0.5$	T _c =110°C	Per diode	100	A
I _{FSM}	Surge non repetitive forward current	tp=10ms sinusoidal	Per diode	1600	A
T _{Stg} T _J	Storage and junction temperature range			- 40 to + 150 - 40 to + 150	°C °C

Symbol	Parameter	Value	Unit
V _{RRM}	Repetitive peak reverse voltage	200	V

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BYV255V

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
R _{th} (j-c)	Junction to case	Per diode	0.4
		Total	0.25
R _{th} (c)	Coupling	0.1	°C/W

When the diodes 1 and 2 are used simultaneously :

$$T_j - T_c \text{ (diode 1)} = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

ELECTRICAL CHARACTERISTICS (Per diode)

STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
I _R *	T _j = 25°C	V _R = V _{RRM}			100	μA
	T _j = 100°C				10	mA
V _F **	T _j = 125°C	I _F = 100 A			0.85	V
	T _j = 125°C	I _F = 200 A			1.00	
	T _j = 25°C	I _F = 200 A			1.15	

Pulse test : * tp = 5 ms, duty cycle < 2 %

** tp = 380 μs, duty cycle < 2 %

RECOVERY CHARACTERISTICS

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
trr	T _j = 25°C	I _F = 0.5A	I _{rr} = 0.25A			55	ns
		I _F = 1A V _R = 30V	dI _F /dt = -50A/μs			80	
irr	T _j = 25°C	I _F = 1A V _{FR} = 1.1 × V _F	tr = 5 ns		10		ns
V _{FP}	T _j = 25°C	I _F = 1A	tr = 5 ns		1.5		V

TURN-OFF SWITCHING CHARACTERISTICS

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
I _{RM}	T _j = 100°C	I _F = 100A L _p Ⓢ 0.05μH V _{cc} Ⓢ 0.6 V _{RRM}	dI _F /dt = -200A/μs			16	A
			dI _F /dt = -400A/μs			24	

Fig.1 : Average forward power dissipation versus average forward current.

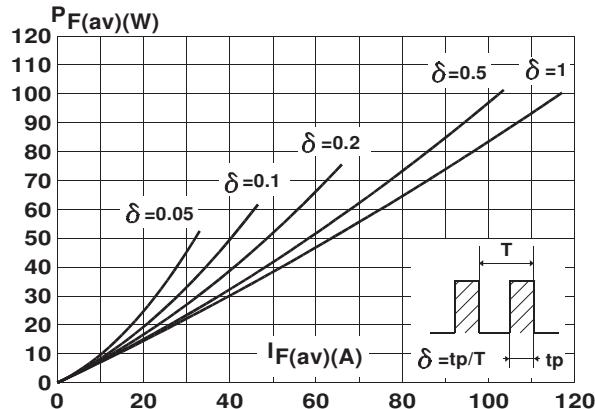


Fig.3 : Forward voltage drop versus forward current (maximum values).

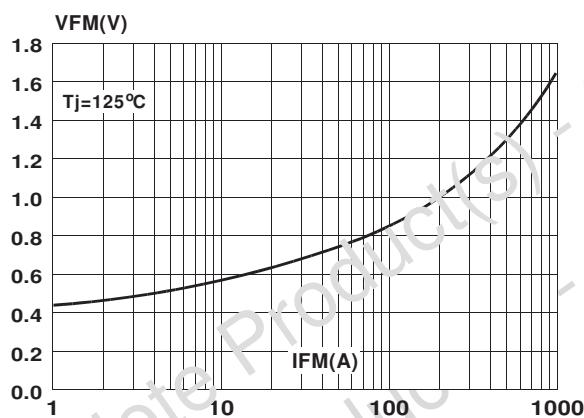


Fig.5 : Non repetitive surge peak forward current versus overload duration.

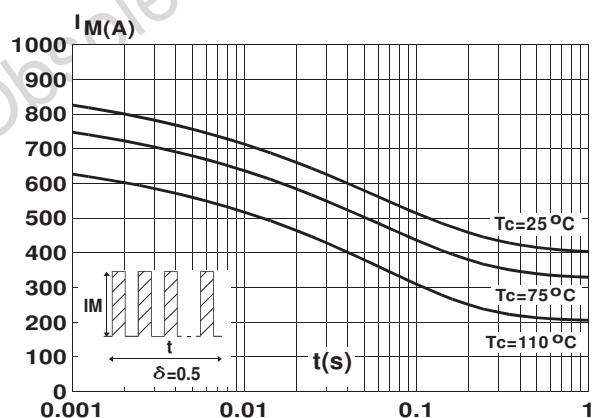


Fig.2 : Peak current versus form factor.

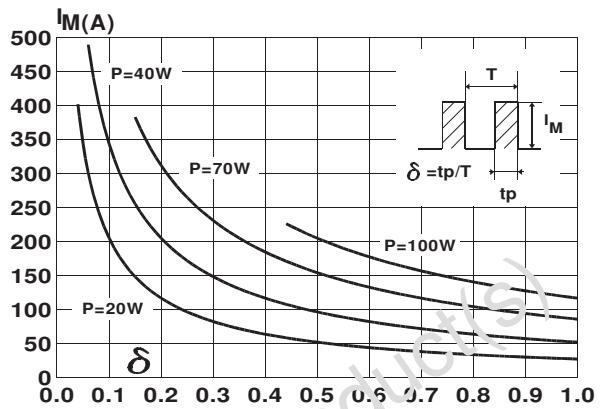


Fig.4 : Relative variation of thermal impedance junction to case versus pulse duration.

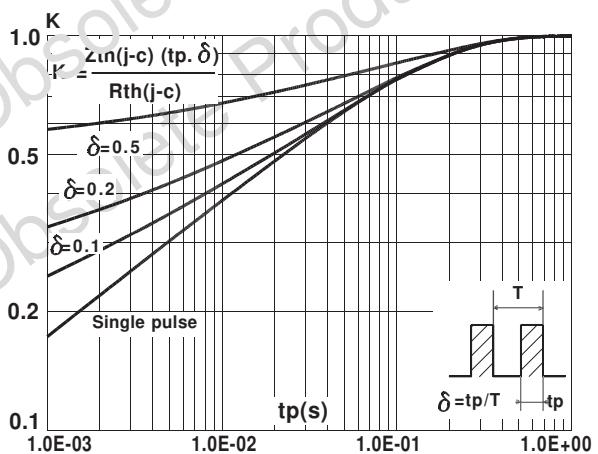
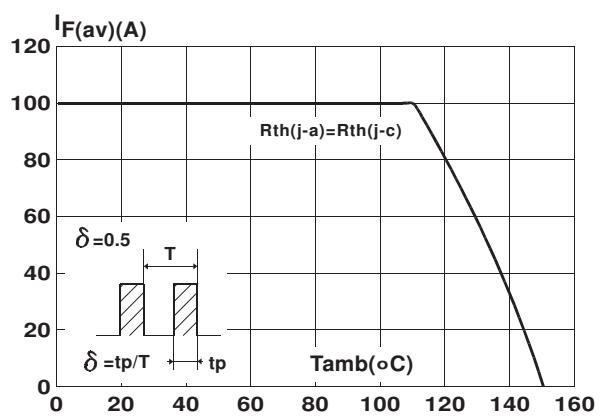


Fig.6 : Average current versus ambient temperature. (duty cycle : 0.5)



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Fig.7 : Junction capacitance versus reverse voltage applied (Typical values).

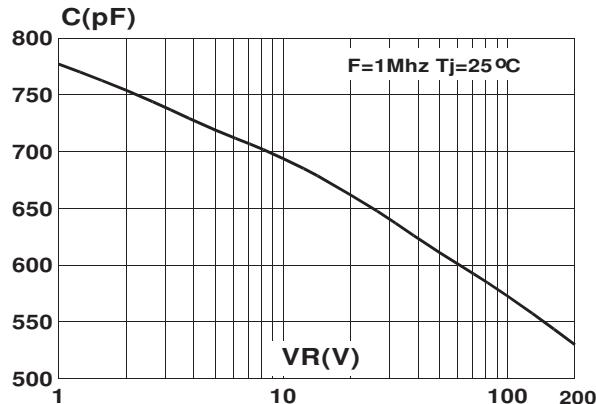


Fig.9 : Peak reverse current versus dIF/dt.

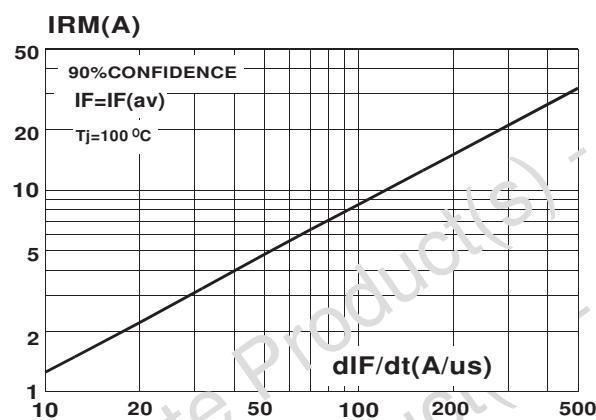


Fig.8 : Recovery charges versus dIF/dt.

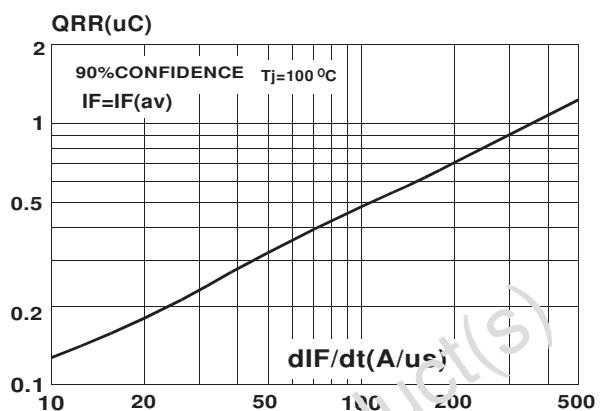
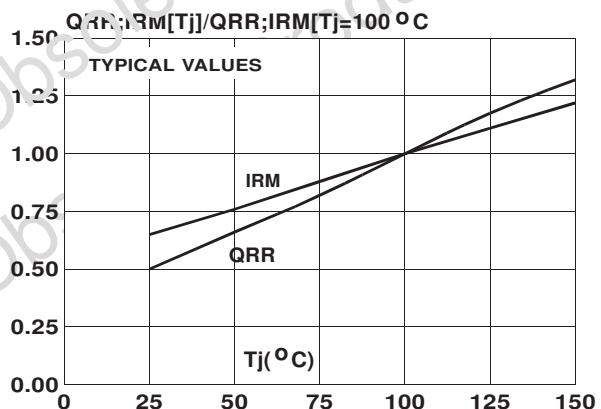
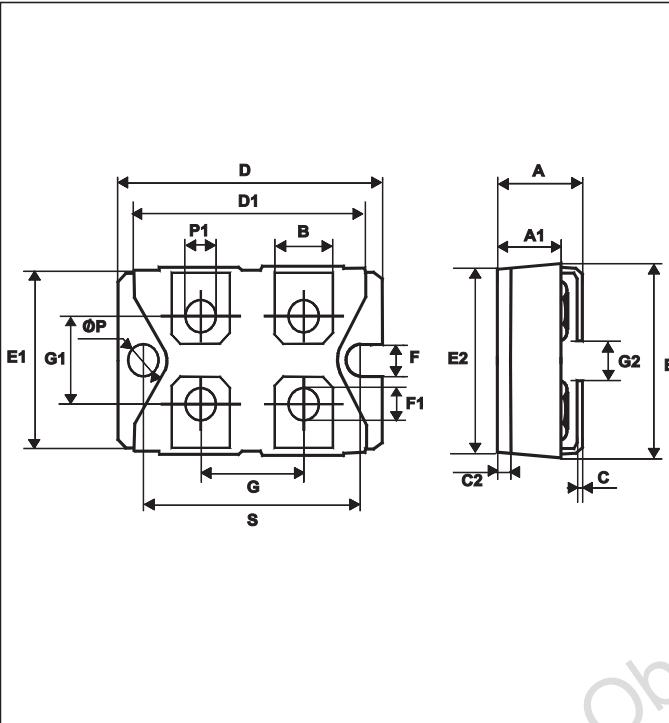


Fig.10 : Dynamic parameters versus junction temperature.



PACKAGE MECHANICAL DATA
 ISOTOP



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	11.80	12.20	0.465	0.480
A1	8.90	9.10	0.350	0.358
B	7.8	8.20	0.307	0.323
C	0.75	0.85	0.030	0.033
C2	1.95	2.05	0.077	0.081
D	37.80	38.20	1.488	1.504
D1	31.50	31.70	1.240	1.248
E	25.15	25.50	0.990	1.004
E1	23.85	24.15	0.939	0.951
E2	24.80 typ.		0.976 typ.	
G	14.90	15.10	0.587	0.594
G1	12.60	12.80	0.496	0.504
G2	3.50	4.30	0.138	0.169
F	4.10	4.30	0.161	0.169
F1	4.60	5.00	0.181	0.197
P	4.00	4.30	0.157	0.69
P1	4.00	4.40	0.157	0.173
S	30.10	30.30	1.185	1.193

- **Marking :** Type number
- **Cooling method :** C
- **Weight :** 27 g
- **Epoxy meets UL94, V0**

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